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WHAT IS CLAIMED IS:

1 1. A display device in which a thin film transistor is  
2 disposed on an insulative substrate, said thin film  
3 transistor comprising:

4 a first gate electrode; a gate insulating film; a  
5 semiconductor film which is formed on said gate insulating  
6 film and which has a channel;

7 a insulating film;

8 a display electrode connected to a source which is  
9 formed in said semiconductor film, said display electrode  
10 being elongated so as to extend above said channel of said  
11 thin film transistor, and

12 wherein a second gate electrode formed between said  
13 first gate electrode and said display electrode.

14

15 2. A display device in which a thin film transistor is  
16 disposed on an insulative substrate, said thin film  
17 transistor comprising:

18 a first gate electrode; a gate insulating film; a  
19 semiconductor film which is formed on said gate insulating  
20 film and which has a channel;

21 a insulating film;

22 a display electrode connected to a source which is  
23 formed in said semiconductor film, said display electrode  
24 being elongated so as to extend above said channel of said

25 thin film transistor, and

26 a second gate electrode formed between said first gate  
27 electrode and said display electrode,

28 wherein said second gate electrode is connected with  
29 said first gate electrode.

30

31 3. A display device according to claim 2, wherein said  
32 second gate electrode is formed so as to be faced with said  
33 first gate electrode through said insulating film.

34

35 4. A display device according to claim 3, wherein said  
36 display electrode is rectangular.

1

1 5. A display device according to claim 1, wherein said  
2 channel is covered with a stopper insulating film.

1

1 6. A display device according to claim 5, wherein said  
2 stopper insulating film is made of an SiO<sub>2</sub> film.

1

1 7. A display device according to claim 5, wherein said  
2 stopper insulating film is made of a two-layered film of  
3 SiN and organic film.

1

2 8. A display device according to claim 1, wherein said  
3 first gate electrode is a double gate structured electrode

4 divided above the channel.

1  
1 9. A display device according to claim 8, wherein said  
2 second gate electrode is a double gate structured electrode  
3 divided corresponding to said first gate electrode.

1  
1 10. A display device according to claim 1, wherein said  
2 display electrode is a reflective display electrode which  
3 is made of a reflective material.

1  
1 11. A display device according to claim 10, wherein said  
2 reflective display electrode is made of Al-Nd alloy.

1  
1 12. A display device according to claim 1, wherein said  
2 display electrode is an electrode used in a liquid display  
3 device.

4  
5 13. A display device according to claim 1, wherein a light  
6 emitting layer is formed on said display electrode, and  
7 said display electrode used in an organic electro  
8 luminescent device.

1  
1 14. A display device according to claim 1, wherein said  
2 thin film transistor further comprising:  
3 a storage capacity electrode which constitute a

4 capacitance;

5 wherein one side of the storage capacity electrode is  
6 made of same material of the first gate electrode.

7

8 15. A display device according to claim 2, wherein a light  
9 emitting layer is formed on said display electrode, and  
10 said display electrode used in an organic electro  
11 luminescent device.

1

1 16. A display device according to claim 2, wherein said  
2 thin film transistor further comprising:

3 a storage capacity electrode which constitute a  
4 capacitance;

5 wherein one side of the storage capacity electrode is  
6 made of same material of the first gate electrode.

7

8 17. A display device comprising:

9 an insulative substrate,

10 a thin film transistor including a gate electrode, a  
11 gate insulating film and a channel region;

12 a display electrode connected to one of a source  
13 region of the thin film transistor and a drain region of  
14 the thin film transistor, said display electrode being  
15 extended above the channel region of the thin film  
16 transistor;

17 an electrode provided between the channel region of  
18 the thin film transistor and the display electrode,  
19 wherein the electrode is connected to the gate  
20 electrode.

21  
22 18. The display device according to claim 17, wherein said  
23 display electrode is a reflective display electrode made of  
24 a reflective material.

25  
26 19. A display device according to claim 17, wherein a light  
27 emitting layer is formed on said display electrode, and  
28 said display electrode used in an organic electro  
29 luminescent device.

1

1 20. A display device according to claim 17, further  
2 comprising:

3 a storage capacity electrode which constitute a  
4 capacitance;

5 wherein one side of the storage capacity electrode is  
6 made of same material of the first gate electrode.

7

8 21. A display device comprising:

9 an insulative substrate,

10 a thin film transistor including a gate electrode, a  
11 gate insulating film and a channel region;

12 a display electrode connected to one of a source  
13 region of the thin film transistor and a drain region of  
14 the thin film transistor, said display electrode being  
15 extended above the channel region of the thin film  
16 transistor;

17 an electrode provided between the channel region of  
18 the thin film transistor and the display electrode,

19 wherein a gate voltage is applied to the electrode.  
20

21 22. The display device according to claim 21, wherein said  
22 display electrode is a reflective display electrode made of  
23 a reflective material.  
24

25 23. A display device according to claim 22, wherein a light  
26 emitting layer is formed on said display electrode, and  
27 said display electrode used in an organic electro  
28 luminescent device.

1

1 24. A display device according to claim 22, further  
2 comprising:

3 a storage capacity electrode which constitute a  
4 capacitance;

5 wherein one side of the storage capacity electrode is  
6 made of same material of the first gate electrode.